

RELIABILITY REPORT
FOR
MAX791ESE+
PLASTIC ENCAPSULATED DEVICES

February 18, 2010

MAXIM INTEGRATED PRODUCTS

120 SAN GABRIEL DR.
SUNNYVALE, CA 94086

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| Approved by |
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| Quality Assurance |
| Director, Reliability Engineering |

Conclusion

The MAX791ESE+ successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards.

Table of Contents

| | |
|--|---|
| I.Device Description | V.Quality Assurance Information |
| II.Manufacturing Information | VI.Reliability Evaluation |
| III.Packaging Information | IV.Die Information |
|Attachments | |

I. Device Description

A. General

The MAX791 microprocessor (μ P) supervisory circuit reduces the complexity and number of components needed to monitor power-supply and battery-control functions in μ P systems. The 50 μ A supply current makes the MAX791 ideal for use in portable equipment, while the 6ns chip-enable propagation delay and 250mA output capability (25mA in battery-backup mode) make it suitable for larger, higher-performance equipment. The MAX791 comes in 16-pin DIP and narrow SO packages and provides the following functions:

- μ P reset-RESET-bar output is asserted during power-up, power-down, and brownout conditions, and is guaranteed to be in the correct state for V_{CC} down to 1V, even with no battery in the circuit.
- Manual-reset input.
- A 1.25V threshold detector provides for power-fail warning and low-battery detection, or monitors a power supply other than +5V.
- Two-stage power-fail warning-a separate low-line comparator compares V_{CC} to a threshold 150mV above the reset threshold.
- Backup-battery switchover for CMOS RAM, real-time clocks, μ Ps, or other low-power logic.
- Software monitoring of backup-battery voltage.
- A watchdog-fault output is asserted if the watchdog input has not been toggled within either a preset or an adjustable timeout period.
- Write protection of CMOS RAM or EEPROM.
- Pulsed watchdog output, to give advance warning of impending WDO-bar assertion caused by watchdog timeout.

II. Manufacturing Information

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|----------------------------------|------------------------------------|
| A. Description/Function: | Microprocessor Supervisory Circuit |
| B. Process: | S3 |
| C. Number of Device Transistors: | |
| D. Fabrication Location: | Oregon |
| E. Assembly Location: | Malaysia, Philippines, Thailand |
| F. Date of Initial Production: | Pre 1997 |

III. Packaging Information

| | |
|--|--------------------------|
| A. Package Type: | 16-pin SOIC (N) |
| B. Lead Frame: | Copper |
| C. Lead Finish: | 100% matte Tin |
| D. Die Attach: | Conductive |
| E. Bondwire: | Au (1.3 mil dia.) |
| F. Mold Material: | Epoxy with silica filler |
| G. Assembly Diagram: | #05-0701-0574 |
| H. Flammability Rating: | Class UL94-V0 |
| I. Classification of Moisture Sensitivity per JEDEC standard J-STD-020-C | Level 1 |
| J. Multi Layer Theta Ja: | 82.2°C/W |
| K. Multi Layer Theta Jc: | 32°C/W |

IV. Die Information

| | |
|----------------------------|---|
| A. Dimensions: | 70 X 110 mils |
| B. Passivation: | Si ₃ N ₄ /SiO ₂ (Silicon nitride/ Silicon dioxide) |
| C. Interconnect: | Al/0.5%Cu with Ti/TiN Barrier |
| D. Backside Metallization: | None |
| E. Minimum Metal Width: | 3.0 microns (as drawn) |
| F. Minimum Metal Spacing: | 3.0 microns (as drawn) |
| G. Bondpad Dimensions: | 5 mil. Sq. |
| H. Isolation Dielectric: | SiO ₂ |
| I. Die Separation Method: | Wafer Saw |

V. Quality Assurance Information

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|-----------------------------------|---|
| A. Quality Assurance Contacts: | Ken Wendel (Director, Reliability Engineering) Bryan Preeshl (Managing Director of QA) |
| B. Outgoing Inspection Level: | 0.1% for all electrical parameters guaranteed by the Datasheet. 0.1% For all Visual Defects. |
| C. Observed Outgoing Defect Rate: | < 50 ppm |
| D. Sampling Plan: | Mil-Std-105D |

VI. Reliability Evaluation

A. Accelerated Life Test

The results of the 135°C biased (static) life test are shown in Table 1. Using these results, the Failure Rate (λ) is calculated as follows:

$$\lambda = \frac{1}{\text{MTTF}} = \frac{14.685}{192 \times 4340 \times 640 \times 2} \quad (\text{Chi square value for MTTF upper limit})$$

(where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)

$$\lambda = 13.4 \times 10^{-9}$$
$$\lambda = 13.4 \text{ F.I.T. (60\% confidence level @ 25°C)}$$

The following failure rate represents data collected from Maxim's reliability monitor program. Maxim performs quarterly life test monitors on its processes. This data is published in the Reliability Report found at <http://www.maxim-ic.com/qa/reliability/monitor>. Cumulative monitor data for the S3 Process results in a FIT Rate of 0.04 @ 25C and 0.69 @ 55C (0.8 eV, 60% UCL)

B. Moisture Resistance Tests

The industry standard 85°C/85%RH or HAST testing is monitored per device process once a quarter.

C. E.S.D. and Latch-Up Testing

The PS46 die type has been found to have all pins able to withstand a HBM transient pulse of +/-2000 V per Mil-Std 883 Method 3015.7. Latch-Up testing has shown that this device withstands a current of +/-250 mA.

Table 1
Reliability Evaluation Test Results

MAX791ESE+

| TEST ITEM | TEST CONDITION | FAILURE IDENTIFICATION | SAMPLE SIZE | NUMBER OF FAILURES |
|-----------------------------------|---|-------------------------------|-------------|--------------------|
| Static Life Test (Note 1) | | | | |
| | Ta = 135°C Biased Time = 192 hrs. | DC Parameters & functionality | 640 | 6 |
| Moisture Testing (Note 2) | | | | |
| HAST | Ta = 130°C RH = 85% Biased Time = 96hrs. | DC Parameters & functionality | 77 | 0 |
| Mechanical Stress (Note 2) | | | | |
| Temperature Cycle | -65°C/150°C 1000 Cycles Method 1010 | DC Parameters & functionality | 77 | 0 |

Note 1: Life Test Data may represent plastic DIP qualification lots.

Note 2: Generic Package/Process data